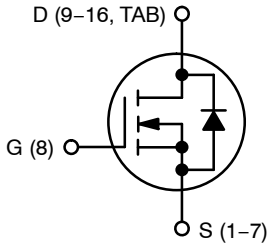
MOSFET - Power, Single N-Channel, STD Gate, TCPAK1012

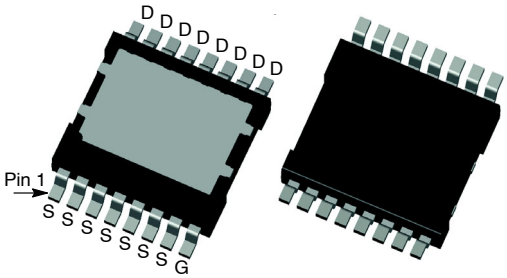
80 V, 1.19 mΩ, 467 A

NVBYST001N08X

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
80 V	1.19 mΩ @ V_{GS} = 10 V	467 A



N-CHANNEL MOSFET



TCPAK1012
(TopCool)
CASE 762AA

Features

- Low Q_{RR}, Soft Recovery Body Diode
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Synchronous Rectification (SR) in DC-DC and AC-DC
- Primary Switch in Isolated DC-DC Converter
- Motor Drives
- Automotive 48V System

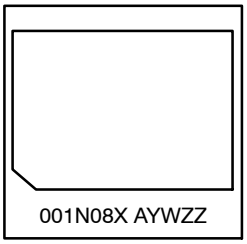
MAXIMUM RATINGS (T_J = 25 °C unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DSS}	80	V
Gate-to-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25 °C	I_D	467	A
	T_C = 100 °C		330	
Power Dissipation	T_C = 25 °C	P_D	517	W
Pulsed Drain Current	T_C = 25 °C, t_p = 100 μs	I_{DM}	1318	A
Operating Junction and Storage Temperature Range		T_J, T_{STG}	−55 to +175	°C
Continuous Source-Drain Current (Body Diode)		I_S	872	A
Single Pulse Avalanche Energy (I_{PK} = 103 A)		E_{AS}	530	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)		T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using a 1 in^2, 1 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
3. E_{AS} is based on started T_J = 25 °C, rated I_{AS}, V_{DD} = 64 V, V_{GS} = 10 V, 100% avalanche tested.

MARKING DIAGRAM



001N08X = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NVBYST001N08XTXG	TCPAK1012	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Top)	$R_{\theta JC}$	0.29	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	38	
Thermal Characterization Parameter, Junction-to-Source Lead (Pin 1−7)*	Ψ_{JL}	4.7	
Thermal Characterization Parameter, Junction-to-Drain Lead (Pin 9−16)*	Ψ_{JL}	3.4	

* Low thermal conductivity test boards compliant with JEDEC Standard 51-3 for leaded surface-mount packages. 1s0p PCB board with a 1 in^2 copper plane, tested under natural convection conditions.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	I_D = 1 mA, Referenced to 25 °C		31		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V, T_J = 25 °C			1.0	μA
		V_{DS} = 80 V, T_J = 125 °C			250	
Gate-to-Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V			100	nA
ON CHARACTERISTICS						
Drain-to-Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 80 A, T_J = 25 °C		1.01	1.19	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 472 μA, T_J = 25 °C	2.4		3.6	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)}/\Delta T_J$	V_{GS} = V_{DS}, I_D = 472 μA		−7.5		mV/°C
Forward Transconductance	g_{FS}	V_{DS} = 5 V, I_D = 80 A		274		S
CHARGES, CAPACITANCES & GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{GS} = 0 V, V_{DS} = 40 V, f = 1 MHz		8678		pF
Output Capacitance	C_{OSS}			2490		
Reverse Transfer Capacitance	C_{RSS}			37		
Output Charge	Q_{OSS}			178		nC
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DD} = 40 V, I_D = 80 A		121		
Threshold Gate Charge	$Q_{G(TH)}$			26		
Gate-to-Source Charge	Q_{GS}			40		
Gate-to-Drain Charge	Q_{GD}			19		
Gate Plateau Voltage	V_{GP}			4.7		V
Gate Resistance	R_G	f = 1 MHz		0.35		Ω
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	Resistive Load, V_{GS} = 0/10 V, V_{DD} = 64 V, I_D = 80 A, R_G = 2.5 Ω		38		ns
Rise Time	t_r			25		
Turn-Off Delay Time	$t_{d(OFF)}$			68		
Fall Time	t_f			11		
SOURCE-TO-DRAIN DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 80 A, T_J = 25 °C		0.81	1.2	V
		V_{GS} = 0 V, I_S = 80 A, T_J = 125 °C		0.65		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, V_{DD} = 64 V, dI/dt = 1000 A/μs, I_S = 80 A		48		ns
Charge Time	t_a			25		
Discharge Time	t_b			23		
Reverse Recovery Charge	Q_{RR}			506		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

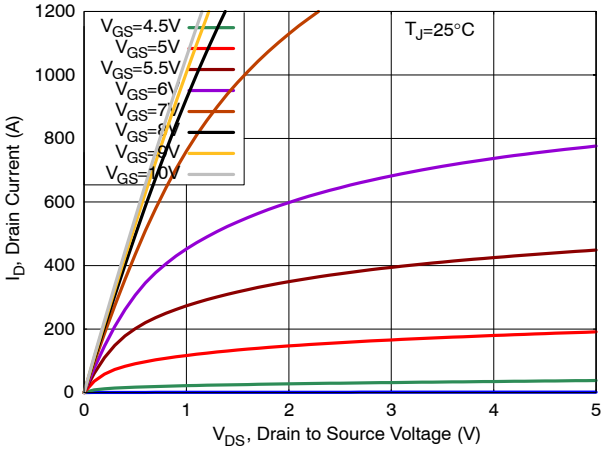


Figure 1. On−Region Characteristics

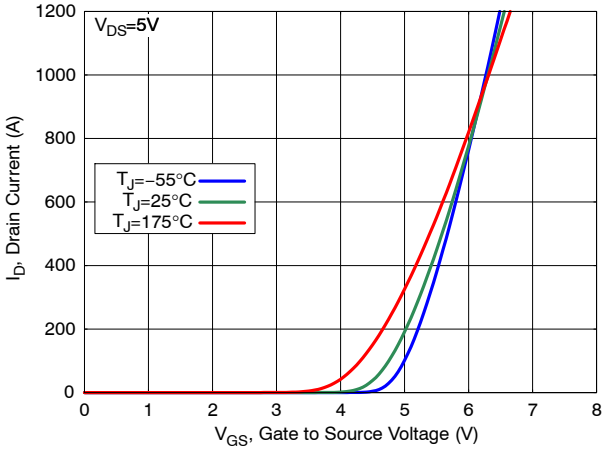


Figure 2. Transfer Characteristics

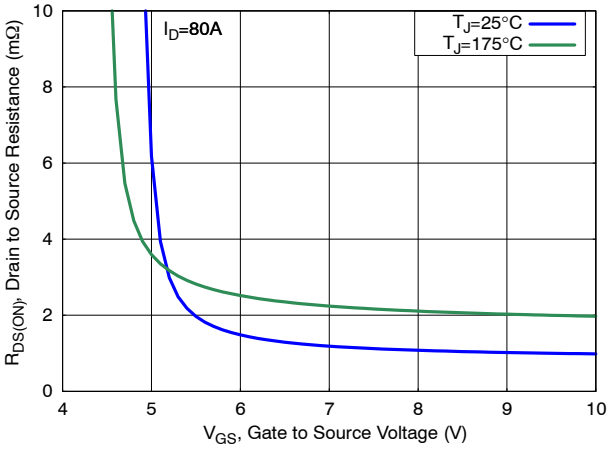


Figure 3. On−Resistance vs. Gate Voltage

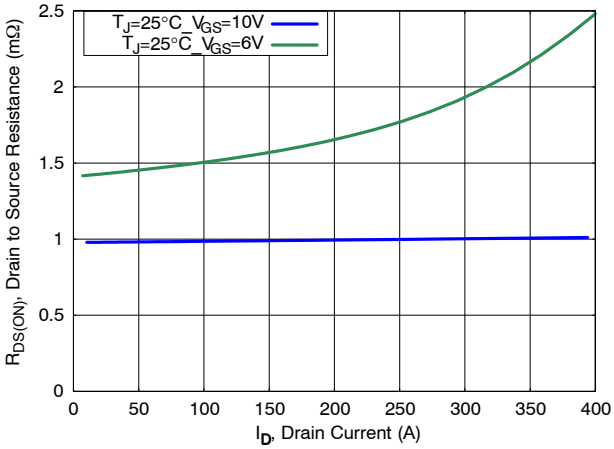


Figure 4. On−Resistance vs. Drain Current

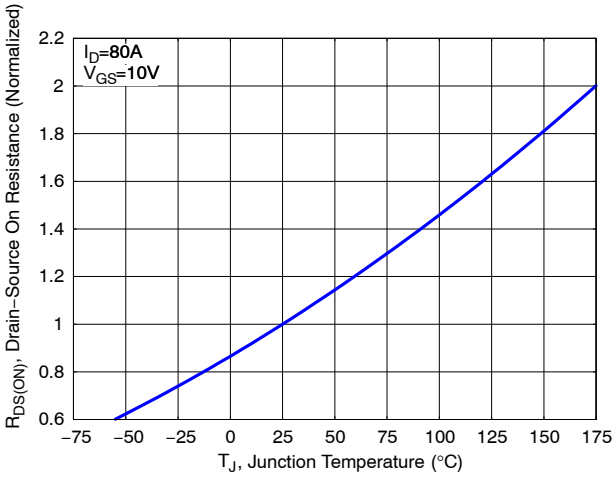


Figure 5. Normalized ON Resistance vs. Junction Temperature

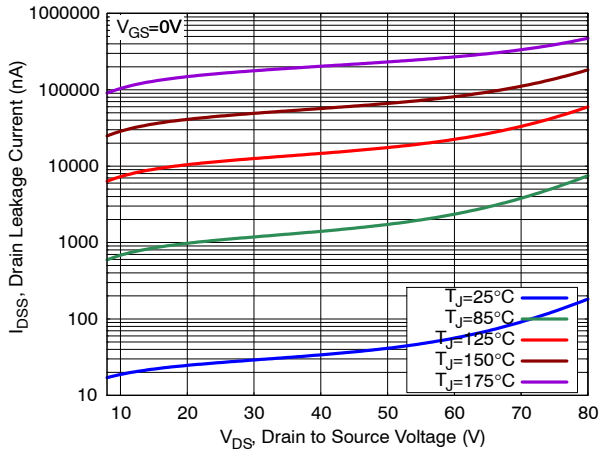


Figure 6. Drain Leakage Current vs. Drain Voltage

TYPICAL CHARACTERISTICS

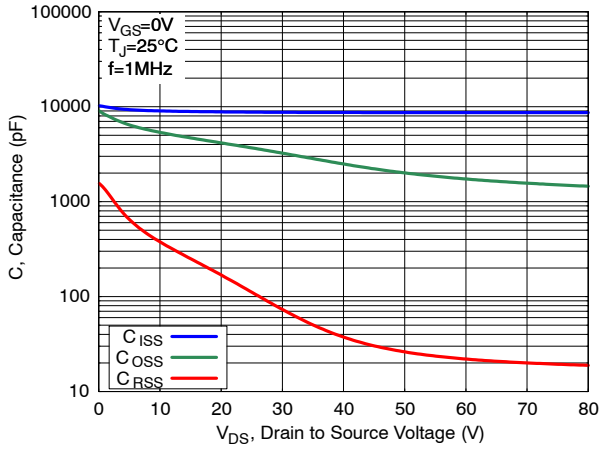


Figure 7. Capacitance Characteristics

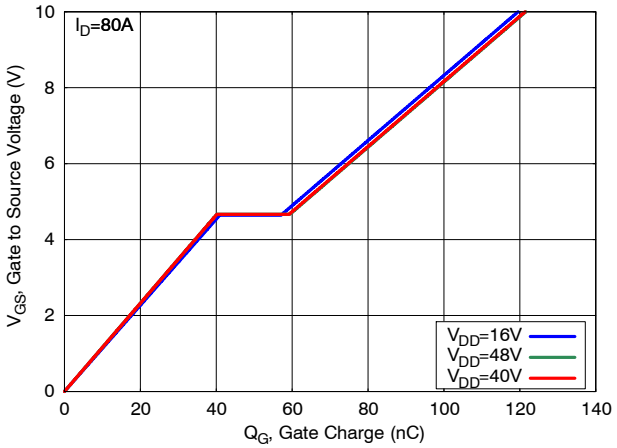


Figure 8. Gate Charge Characteristics

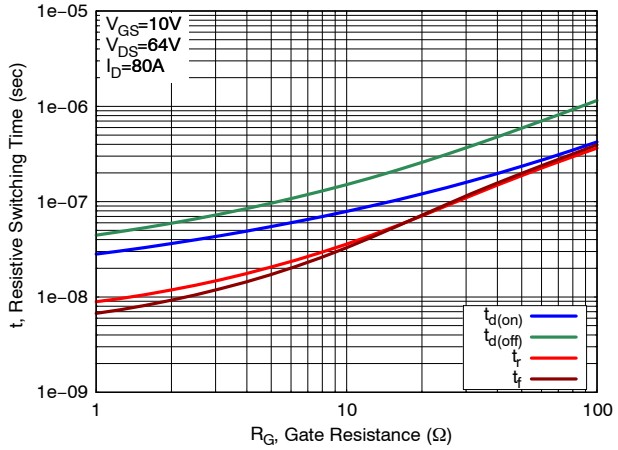


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

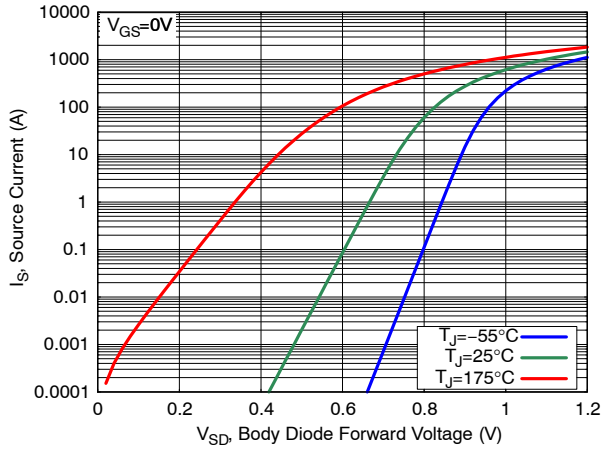


Figure 10. Diode Forward Characteristics

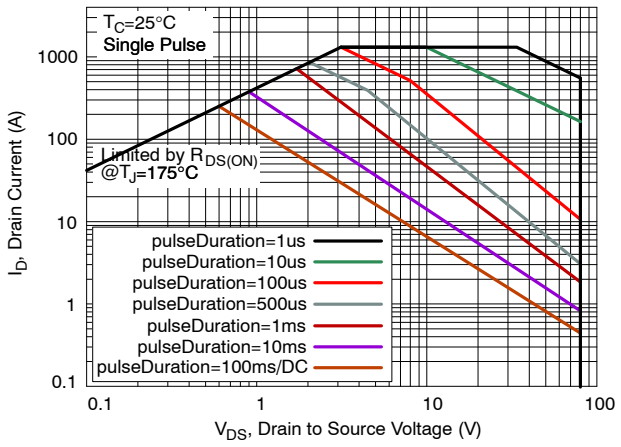


Figure 11. Safe Operating Area (SOA)

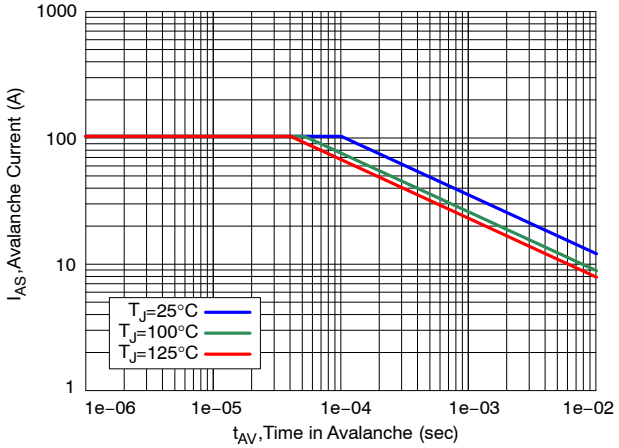


Figure 12. Avalanche Current vs. Pulse Time (UIS)

TYPICAL CHARACTERISTICS

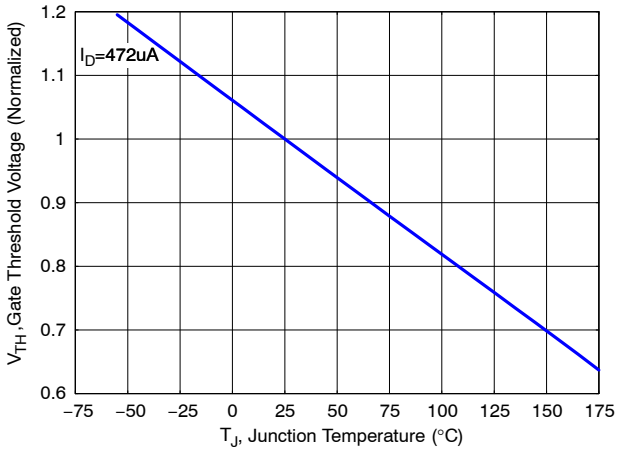


Figure 13. Gate Threshold Voltage vs. Junction Temperature

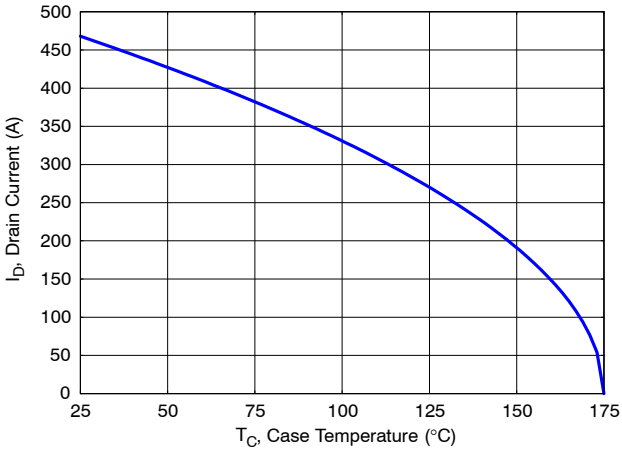


Figure 14. Maximum Current vs. Case Temperature

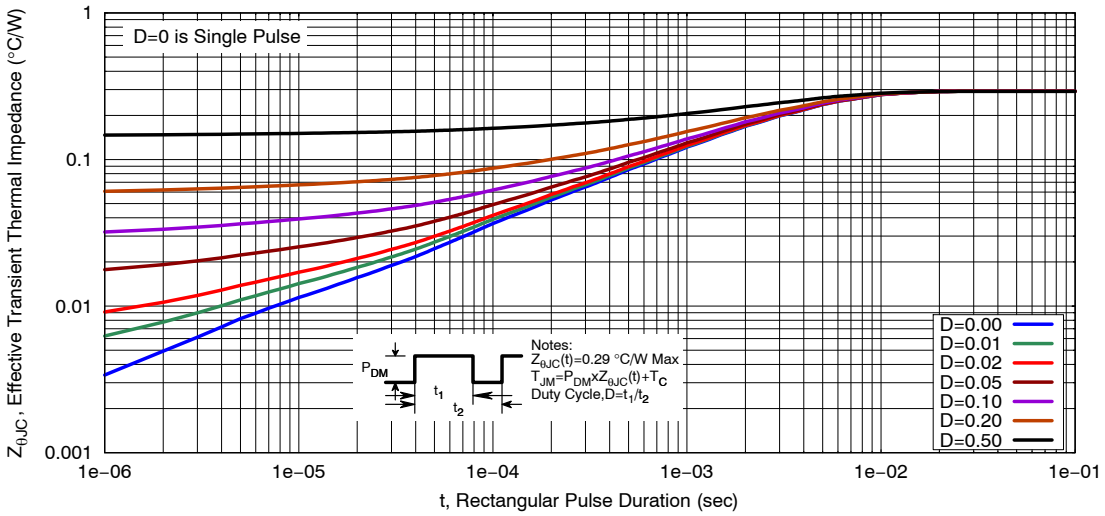


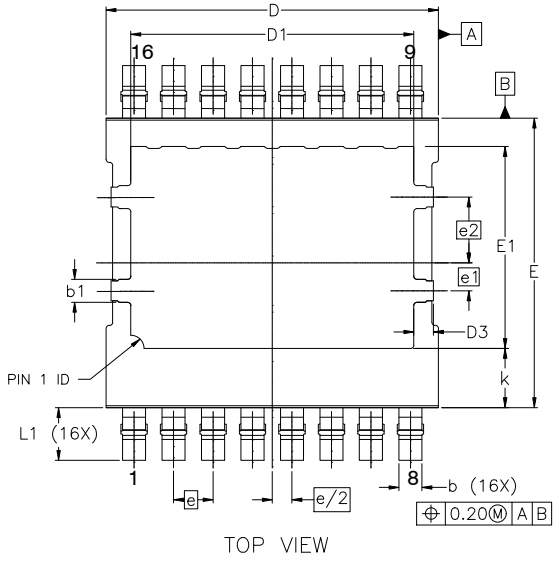
Figure 15. Transient Thermal Response

REVISION HISTORY

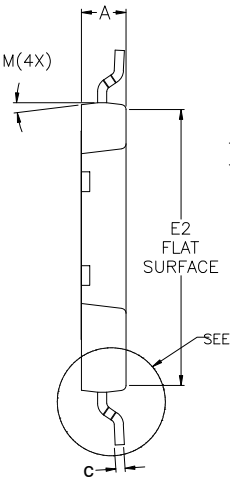
Revision	Description of Changes	Date
P0	Initial Revision	5/29/2024
P1	Maximum Rdxson changed from 1.2 to 1.9mohm Pdmax changed from 600W to 517W (also changed related items − max ID, IDM) Rthjc changed from 0.25 to 0.29degC/W IPK at avalanche event changed from 160A to 103A (Eas also changed from 1280 to 530mJ) switching characteristics were updated based on the CZ data Reverse recovery characteristics were updated based on the CZ data SOA and UIS curve characteristics werer updated based on the CZ data Case image updated on the front page	5/22/2025
0	Remove product preview, add bullet, add to the thermal characteristics table, replace figures 3, 4, 6, 9 and 15	8/27/2025
1	Typical Rdson change from 0.98 to 1.01 mΩ	10/2/2025

PACKAGE DIMENSIONS

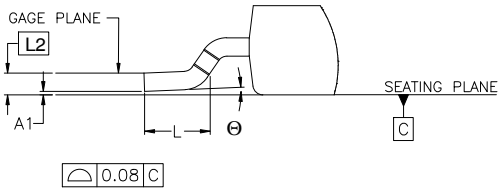
TCPAK16 8.80x10.10, 1.20P (TCPAK1012)
CASE 762AA
ISSUE E



TOP VIEW

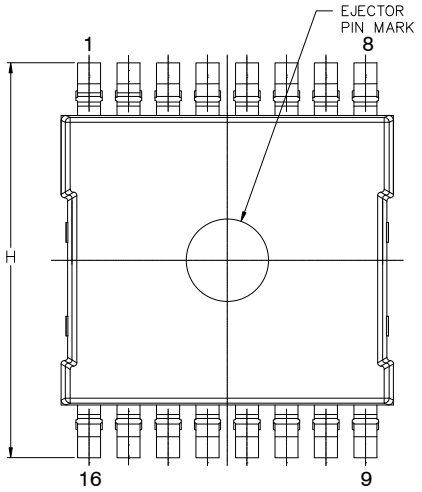


SIDE VIEW

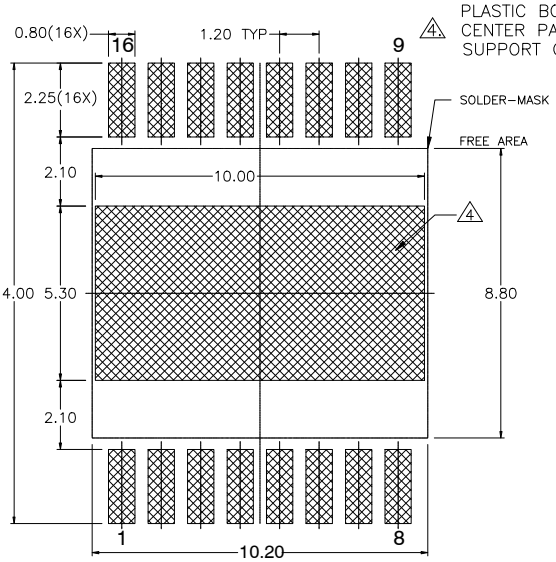


DETAIL 'A'

NOTES:
1. UNIT DIMENSION: MILLIMETER
2. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR MOLD GATE REMAINS. MOLD FLASH OR GATE REMAINS SHALL NOT EXCEED 0.150mm PER SIDE.
3. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
4. CENTER PAD IS FOR PKG MECHANICAL SUPPORT ONLY. NO SOLDERING REQUIRED.



BOTTOM VIEW

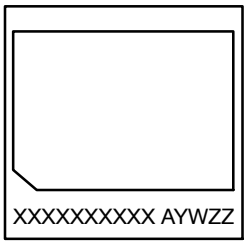


LAND PATTERN RECOMMENDATION

MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.30	1.35	1.40
A1	0.00	0.05	0.10
b	0.67	0.72	0.77
b1	0.65	0.70	0.75
c	0.21	0.26	0.31
D	10.00	10.10	10.20
D1	8.50	8.60	8.70
D3	0.55	0.60	0.75
E	8.70	8.80	8.90
E1	6.04	6.14	6.24
E2	---	---	8.70
e	1.20 BSC		
e/2	0.60 BSC		
e1	0.85 BSC		
e2	2.00 BSC		
k	1.70	1.80	1.90
H	11.80	12.00	12.20
L	0.80	1.00	1.20
L1	1.40	1.60	1.80
L2	0.30 BSC		
Θ	–	2.5°	5°

*For additional information on our Pb−Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

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